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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Jean-Michel Daga et al. PATENT APPLICATION
Serial No.: 10/810,033 Group Art Unit: 2816
Filed: March 26, 3004
For: HIGH EFFICIENCY, LOW COST, CHARGE PUMP CIRCUIT

Supplemental Information Disclosure Statement
with Certification under 37 CFR § 1.97(e)(1)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following information is submitted in compliance with Applicants' duty of disclosure under 37 CFR § 1.97(e). A copy of the cited reference is enclosed.

Other Reference

Article entitled "A New High Efficiency CMOS Voltage Doubler" by Pierre Favrat et al., Swiss Federal Institute of Technology, Electronics Labs EL-LEG, Ecublens, CH-1015 Lausanne, Switzerland and Mead Microelectronics Engineering Applications and Design SA, Venoge 7, CH-1025 St. Sulpice, Switzerland, IEEE 1997 Custom Integrated Circuits Conference, pages 259-262, (0-7803-3669-0).

The undersigned hereby certifies that the item of information contained in this Supplemental Information Disclosure Statement was cited in a communication received from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

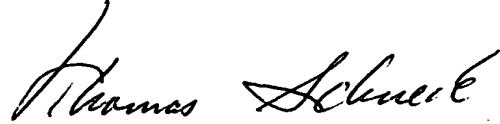
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Signed: Brenda Elmidolan
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Date: December 22, 2004

Respectfully submitted,



Thomas Schneck

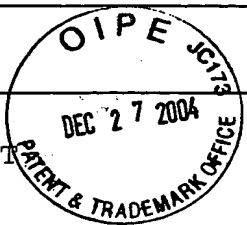
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CITED BY APPLICANTApplicants:
Jean-Michel Daga et al.Filing Date:
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Group: 2816

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Publ. Date	Name	Class	Sub Class	Filing Date
	AA					
	AB					
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FOREIGN PATENT DOCUMENTS

Examiner Initial*	Document Number	Publ. Date	Country	Class	Sub Class	Translation Yes No
	AK					
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	AM					
	AN					

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AO	Article entitled "A New High Efficiency CMOS Voltage Doubler" by Pierre Favrat et al., Swiss Federal Institute of Technology Electronics Labs EL-LEG, Ecublens, CH-1015 Lausanne, Switzerland and Mead Microelectronics Engineering Applications and Design SA, Venoge 7, CH-1025 St. Sulpice, Switzerland, IEEE 1997 Custom Integrated Circuits Conference, pages 259-262 (0-7803-3669-0).
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EXAMINER:

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